

# SEMiX155GD12T4



SEMiX® 5

## Trench IGBT Modules

### Evaluation Sample SEMiX155GD12T4

#### Target Data

#### Features

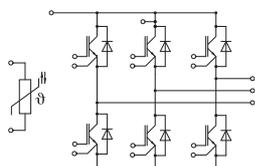
- Solderless assembling solution with PressFIT signal pins and screw power terminals
- IGBT 4 Trench Gate Technology
- $V_{CE(sat)}$  with positive temperature coefficient
- Low inductance case
- Reliable mechanical design with injection moulded terminals and reliable internal connections
- UL recognized file no. E63532
- NTC temperature sensor inside

#### Typical Applications\*

- AC inverter drives
- UPS
- Electronic Welding

#### Remarks

- Product reliability results are valid for  $T_{jop}=150^{\circ}\text{C}$
- Dynamic data are estimated
- For storage and case temperature with TIM see document "TP(HALA P8) SEMiX 5p"



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## Absolute Maximum Ratings

| Symbol      | Conditions                    | Values                      | Unit               |               |
|-------------|-------------------------------|-----------------------------|--------------------|---------------|
| <b>IGBT</b> |                               |                             |                    |               |
| $V_{CES}$   | $T_j = 25^{\circ}\text{C}$    | 1200                        | V                  |               |
| $I_C$       | $T_j = 175^{\circ}\text{C}$   | $T_c = 25^{\circ}\text{C}$  | 219                | A             |
|             |                               | $T_c = 80^{\circ}\text{C}$  | 169                | A             |
| $I_{Cnom}$  |                               | 150                         | A                  |               |
| $I_{CRM}$   | $I_{CRM} = 3 \times I_{Cnom}$ | 450                         | A                  |               |
| $V_{GES}$   |                               | -20 ... 20                  | V                  |               |
| $t_{psc}$   | $V_{CC} = 800\text{ V}$       | $T_j = 150^{\circ}\text{C}$ | 10                 | $\mu\text{s}$ |
|             | $V_{GE} \leq 20\text{ V}$     |                             |                    |               |
|             | $V_{CES} \leq 1200\text{ V}$  |                             |                    |               |
| $T_j$       |                               | -40 ... 175                 | $^{\circ}\text{C}$ |               |

## Inverse diode

|            |  |                            |                    |   |
|------------|--|----------------------------|--------------------|---|
| $V_{RRM}$  | $T_j = 25^{\circ}\text{C}$                                       | 1200                       | V                  |   |
| $I_F$      | $T_j = 175^{\circ}\text{C}$                                      | $T_c = 25^{\circ}\text{C}$ | 175                | A |
|            |  | $T_c = 80^{\circ}\text{C}$ | 131                | A |
| $I_{Fnom}$ |  | 150                        | A                  |   |
| $I_{FRM}$  | $I_{FRM} = 2 \times I_{Fnom}$                                    | 300                        | A                  |   |
| $I_{FSM}$  | $t_p = 10\text{ ms, sin } 180^{\circ}, T_j = 25^{\circ}\text{C}$ | 900                        | A                  |   |
| $T_j$      |  | -40 ... 175                | $^{\circ}\text{C}$ |   |

## Module

|              |                                   |             |                    |
|--------------|-----------------------------------|-------------|--------------------|
| $I_{t(RMS)}$ |                                   | 280         | A                  |
| $T_{stg}$    | module without TIM                | -40 ... 125 | $^{\circ}\text{C}$ |
| $V_{isol}$   | AC sinus 50Hz, $t = 1\text{ min}$ | 4000        | V                  |

## Characteristics

| Symbol        | Conditions  | min.                        | typ.   | max. | Unit             |
|---------------|---|-----------------------------|--------|------|------------------|
| <b>IGBT</b>   |   |                             |        |      |                  |
| $V_{CE(sat)}$ | $I_C = 150\text{ A}$<br>$V_{GE} = 15\text{ V}$<br>chipelevel                          | $T_j = 25^{\circ}\text{C}$  | 1.80   | 2.05 | V                |
|               |   | $T_j = 150^{\circ}\text{C}$ | 2.20   | 2.40 | V                |
| $V_{CE0}$     | chipelevel  | $T_j = 25^{\circ}\text{C}$  | 0.80   | 0.90 | V                |
|               |   | $T_j = 150^{\circ}\text{C}$ | 0.70   | 0.80 | V                |
| $r_{CE}$      | $V_{GE} = 15\text{ V}$<br>chipelevel  | $T_j = 25^{\circ}\text{C}$  | 6.7    | 7.7  | $\text{m}\Omega$ |
|               |   | $T_j = 150^{\circ}\text{C}$ | 10.0   | 11   | $\text{m}\Omega$ |
| $V_{GE(th)}$  | $V_{GE}=V_{CE}, I_C = 6\text{ mA}$  | 5                           | 5.8    | 6.5  | V                |
| $I_{CES}$     | $V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}, T_j = 25^{\circ}\text{C}$               |                             |        | 2.0  | $\text{mA}$      |
| $C_{ies}$     | $V_{CE} = 25\text{ V}$<br>$V_{GE} = 0\text{ V}$                                       | $f = 1\text{ MHz}$          | 9.3    |      | $\text{nF}$      |
| $C_{oes}$     |   | $f = 1\text{ MHz}$          | 0.58   |      | $\text{nF}$      |
| $C_{res}$     |   | $f = 1\text{ MHz}$          | 0.51   |      | $\text{nF}$      |
| $Q_G$         | $V_{GE} = -15\text{ V} \dots +15\text{ V}$  |                             | 850    |      | $\text{nC}$      |
| $R_{Gint}$    | $T_j = 25^{\circ}\text{C}$  |                             | 5.0    |      | $\Omega$         |
| $t_{d(on)}$   | $V_{CC} = 600\text{ V}$<br>$I_C = 150\text{ A}$                                       | $T_j = 150^{\circ}\text{C}$ | t.b.d. |      | $\text{ns}$      |
| $t_r$         | $V_{GE} = +15/-15\text{ V}$   | $T_j = 150^{\circ}\text{C}$ | t.b.d. |      | $\text{ns}$      |
| $E_{on}$      | $R_{G on} = 1\ \Omega$  | $T_j = 150^{\circ}\text{C}$ | 13     |      | $\text{mJ}$      |
| $t_{d(off)}$  | $R_{G off} = 1\ \Omega$   | $T_j = 150^{\circ}\text{C}$ | t.b.d. |      | $\text{ns}$      |
| $t_f$         | $di/dt_{on} = 3300\text{ A}/\mu\text{s}$<br>$di/dt_{off} = 1000\text{ A}/\mu\text{s}$ | $T_j = 150^{\circ}\text{C}$ | t.b.d. |      | $\text{ns}$      |
|               |   | $T_j = 150^{\circ}\text{C}$ | t.b.d. |      | $\text{ns}$      |
| $E_{off}$     |   | $T_j = 150^{\circ}\text{C}$ | 21     |      | $\text{mJ}$      |
| $R_{th(j-c)}$ | per IGBT  |                             |        | 0.21 | $\text{K/W}$     |
| $R_{th(c-s)}$ | per IGBT ( $\lambda_{grease}=0.81\text{ W/mK}$ ,<br>thickness 50-100 $\mu\text{m}$ )  |                             | t.b.d. |      | $\text{K/W}$     |
| $R_{th(c-s)}$ | per IGBT ( $\lambda=3.4\text{ W/mK}$ )  |                             | t.b.d. |      | $\text{K/W}$     |



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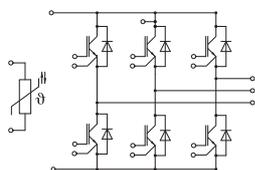
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#### Remarks

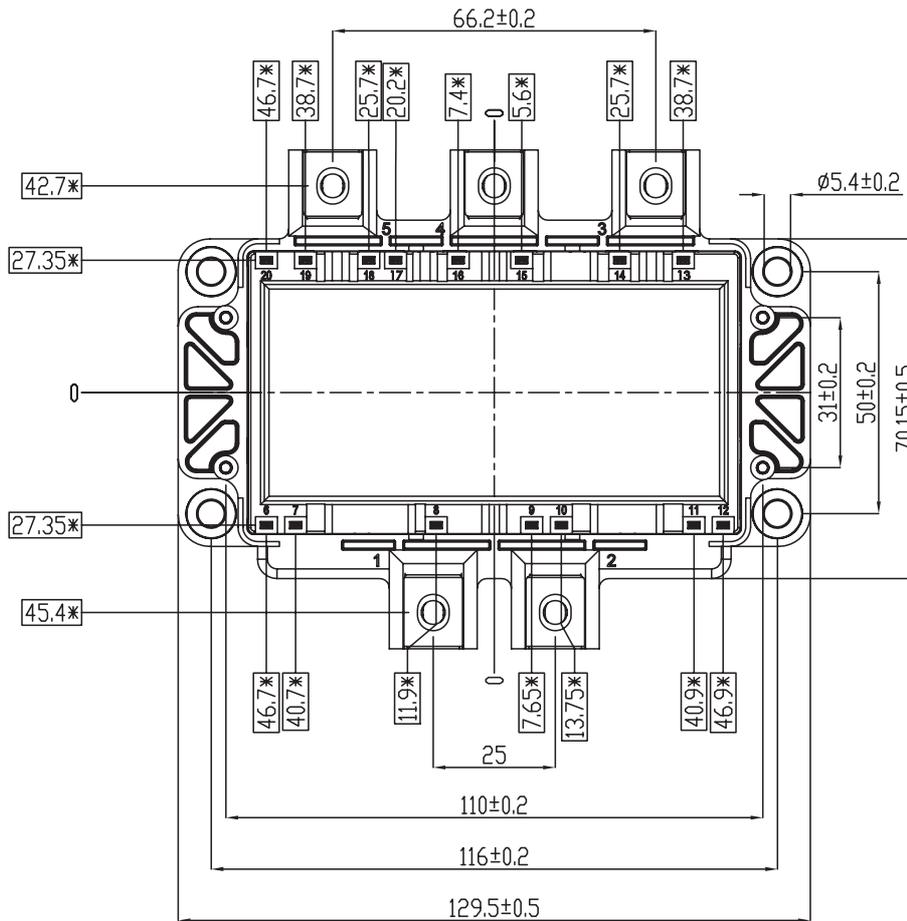
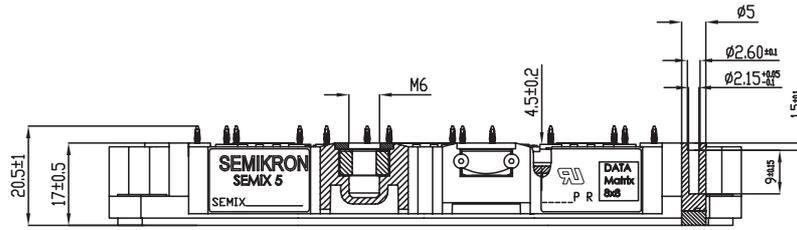
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- For storage and case temperature with TIM see document "TP(HALA P8) SEMiX 5p"

| Characteristics           |   |                             |      |                     |      |               |
|---------------------------|---|-----------------------------|------|---------------------|------|---------------|
| Symbol                    | Conditions  |                             | min. | typ.                | max. | Unit          |
| <b>Inverse diode</b>      |   |                             |      |                     |      |               |
| $V_F = V_{EC}$            | $I_F = 150\text{ A}$<br>$V_{GE} = 0\text{ V}$<br>chipelevel   | $T_j = 25^{\circ}\text{C}$  |      | 2.14                | 2.46 | V             |
|                           |   | $T_j = 150^{\circ}\text{C}$ |      | 2.07                | 2.38 | V             |
| $V_{F0}$                  | chipelevel  | $T_j = 25^{\circ}\text{C}$  |      | 1.30                | 1.50 | V             |
|                           |   | $T_j = 150^{\circ}\text{C}$ |      | 0.90                | 1.10 | V             |
| $r_F$                     | chipelevel  | $T_j = 25^{\circ}\text{C}$  |      | 5.6                 | 6.4  | m $\Omega$    |
|                           |   | $T_j = 150^{\circ}\text{C}$ |      | 7.8                 | 8.5  | m $\Omega$    |
| $I_{RRM}$                 | $I_F = 150\text{ A}$  | $T_j = 150^{\circ}\text{C}$ |      | -                   |      | A             |
| $Q_{rr}$                  | $di/dt_{off} = 3300\text{ A}/\mu\text{s}$   | $T_j = 150^{\circ}\text{C}$ |      | -                   |      | $\mu\text{C}$ |
| $E_{rr}$                  | $V_{GE} = -15\text{ V}$<br>$V_{CC} = 600\text{ V}$  | $T_j = 150^{\circ}\text{C}$ |      | 14                  |      | mJ            |
| $R_{th(j-c)}$             | per diode   |                             |      |                     | 0.35 | K/W           |
| $R_{th(c-s)}$             | per diode ( $\lambda_{grease}=0.81\text{ W/mK}$ ,<br>thickness 50-100 $\mu\text{m}$ )   |                             |      | t.b.d.              |      | K/W           |
| $R_{th(c-s)}$             | per diode ( $\lambda=3.4\text{ W/mK}$ )   |                             |      | t.b.d.              |      | K/W           |
| <b>Module</b>             |   |                             |      |                     |      |               |
| $L_{CE}$                  |   |                             |      | 20                  |      | nH            |
| $R_{CC+EE}$               | measured per<br>switch  | $T_C = 25^{\circ}\text{C}$  |      | 1.2                 |      | m $\Omega$    |
|                           |   | $T_C = 125^{\circ}\text{C}$ |      | 1.65                |      | m $\Omega$    |
| $R_{th(c-s)1}$            | calculated without thermal coupling   |                             |      | t.b.d.              |      | K/W           |
| $R_{th(c-s)2}$            | including thermal coupling,<br>$T_s$ underneath module ( $\lambda_{grease}=0.81\text{ W}/$<br>( $\text{m}^{\circ}\text{K}$ )) |                             |      | t.b.d.              |      | K/W           |
| $R_{th(c-s)2}$            | including thermal coupling,<br>$T_s$ underneath module, pre-applied<br>phase change material                                  |                             |      | t.b.d.              |      | K/W           |
| $M_s$                     | to heat sink (M5)   |                             | 3    |                     | 6    | Nm            |
| $M_t$                     |   | to terminals (M6)           | 3    |                     | 6    | Nm            |
|                           |   |                             |      |                     |      | Nm            |
| $w$                       |   |                             |      | 398                 |      | g             |
| <b>Temperature Sensor</b> |   |                             |      |                     |      |               |
| $R_{100}$                 | $T_c=100^{\circ}\text{C}$ ( $R_{25}=5\text{ k}\Omega$ )   |                             |      | $493 \pm 5\%$       |      | $\Omega$      |
| $B_{100/125}$             | $R_{(T)}=R_{100}\exp[B_{100/125}(1/T-1/T_{100})]$ ; $T[\text{K}]$ ;   |                             |      | $3550$<br>$\pm 2\%$ |      | K             |



GD

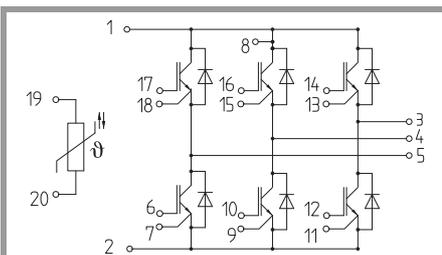
# SEMiX155GD12T4



\* = All dimension with tolerance of  $\begin{matrix} \oplus \\ \ominus \end{matrix} \begin{matrix} \oplus \\ \ominus \end{matrix} 0,4$

For technical details please refer to SEMiX(R)5 Mounting Instruction

SEMiX5p



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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

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